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F1  
a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second metallic layer at the bottom of a contact hole provided in said second insulating film,

wherein said conductive layer and said second metallic layer are directly connected to each other through a contact hole provided in said first metallic layer and said first insulating film.

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7. (Third Amendment) A semiconductor device comprising:

F2  
a first insulating film comprising an organic material formed over a thin film transistor;

a first metallic layer formed on said first insulating film;

a second metallic layer formed on said first metallic layer;

a second insulating film formed on said second metallic layer; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second metallic layer at the bottom of a contact hole provided in said second insulating film,

wherein a source region or a drain region of said thin film transistor and said second metallic layer are directly connected to each other through a contact hole provided in said first metallic layer and said first insulating film.

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19. (Third Amendment) A semiconductor device comprising:

F3  
a first insulating film comprising an organic material formed over a thin film transistor;

a first conductive layer formed on said first insulating film;

a second conductive layer formed on said first conductive layer;

a second insulating film formed on said second conductive layer; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer at the bottom of a contact hole provided in said second insulating film,

wherein a source region or a drain region and said second conductive layer are directly connected to each other through a contact hole provided in said first conductive layer and said first insulating film,

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1-3

wherein said second conductive layer is contact with said first insulating film inside of said contact hole.

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28. (Fourth Amendment) A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

a first insulating film formed over said thin film transistor;

a first conductive layer formed on said first insulating film;

a second conductive layer formed on said first conductive layer;

a second insulating film formed on said second conductive layer; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer at the bottom of a contact hole provided in said second insulating film,

wherein said second conductive layer is directly connected to said semiconductor layer through a contact hole provided in said first conductive layer and said first insulating film.

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34. (Fourth Amendment) A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

a first insulating film comprising an organic material formed over said thin film transistor;

a first conductive layer formed on said first insulating film;

a second conductive layer formed on said first conductive layer;

a second insulating film formed on said second conductive layer; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer at the bottom of a contact hole provided in said second insulating film,

wherein said second conductive layer is directly connected to said semiconductor layer through a contact hole provided in said first conductive layer and said first insulating film.

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40. (Twice Amended) A semiconductor device comprising:  
a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

a first insulating film formed over said thin film transistor;

a first wiring formed on said first insulating film;

a second wiring formed on said first wiring;

a second insulating film formed on said second wiring; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second wiring at the bottom of a contact hole provided in said second insulating film,

wherein said second wiring is directly connected to said semiconductor layer through a contact hole provided in said first wiring and said first insulating film.

#### REMARKS

Applicants will address each of the Examiner's rejections in the order in which they appear in the Final Rejection.

#### Claim Rejections – 35 USC §102

In the Final Rejection, the Examiner continues to reject Claims 40, 44 and 45 under 35 USC §102(e) as being anticipated by Yamazaki et al. '818. The Examiner also continues to reject Claims 40 and 44 under 35 USC §102(b) as being anticipated by Zhang '701. Each of these rejections is respectfully traversed.

In order to advance the prosecution of this application and to clarify the invention being claimed, independent Claim 40 has been amended to recite that the second wiring is directly